20 V single N-channel Trench MOSFET 6 July 2012

**Product data sheet** 

## 1. Product profile

#### 1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### **1.2 Features and benefits**

- Trench MOSFET technology
- Very fast switching
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection

#### 1.3 Applications

- Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portables
- Hard disk and computing power management

#### 1.4 Quick reference data

Table 1. Qui	ick reference data						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	20	V
V <sub>GS</sub>	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	$V_{GS}$ = 4.5 V; $T_{amb}$ = 25 °C; t ≤ 5 s	[1]	-	-	11.3	А
Static charact	teristics	·					
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 7.9 A; T <sub>j</sub> = 25 °C		-	14	18	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.





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## 2. Pinning information

Table 2.	Pinning	information			
Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	D	drain		D	
2	D	drain			
3	G	gate		G	
4	S	source		\$ 017aaa253	
5	D	drain	Transparent top view DFN2020MD-6 (SOT1220)	Transparent top view	077442200
6	D	drain			
7	D	drain			
8	S	source			

## 3. Ordering information

Table 3.         Ordering information							
Type number	Package	Package					
	Name	Description	Version				
PMPB12UN	DFN2020MD-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220				

## 4. Marking

Table 4.   Marking codes	
Type number	Marking code
PMPB12UN	1F

## 5. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	20	V
V <sub>GS</sub>	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	$V_{GS}$ = 4.5 V; $T_{amb}$ = 25 °C; t ≤ 5 s	[1]	-	11.3	А
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	7.9	А
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	5	А
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	31	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[1]	-	1.7	W
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Symbol	Parameter	Conditions		Min	Max	Unit
		T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	3.5	W
		T <sub>sp</sub> = 25 °C		-	12.5	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drai	in diode				1	,
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	1.8	А

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

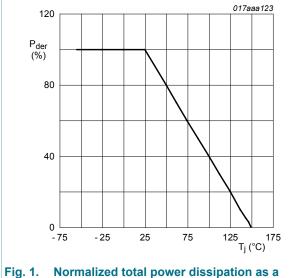


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

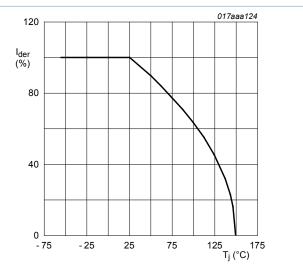
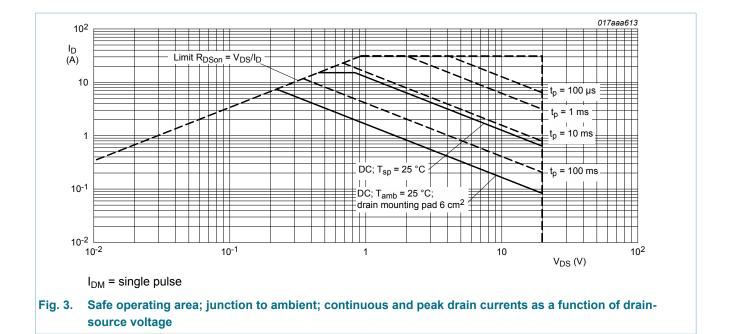


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

#### 20 V single N-channel Trench MOSFET



## 6. Thermal characteristics

Table 6. Th	nermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	235	270	K/W
	from junction to ambient		[2]	-	67	74	K/W
	ampient		[3]	-	33	36	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	5	10	K/W

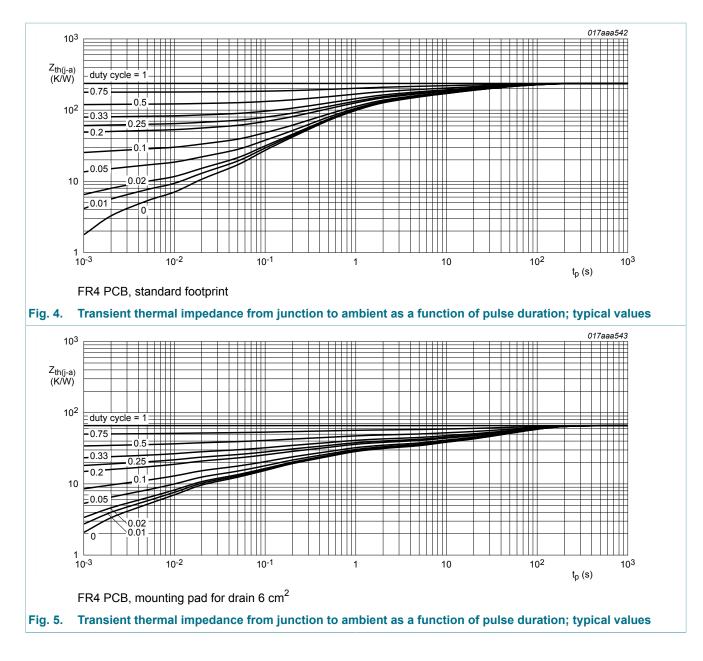
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>, t  $\leq$  5 s

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## 7. Characteristics

Table 7. Ch	naracteristics							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit	
Static characteristics								
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C		20	-	-	V	
V <sub>GSth</sub>	gate-source threshold voltage	I <sub>D</sub> = 250 μA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C		0.4	0.7	1	V	
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 20 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C		-	-	1	μA	
		$V_{DS}$ = 20 V; $V_{GS}$ = 0 V; $T_j$ = 150 °C		-	-	100	μA	
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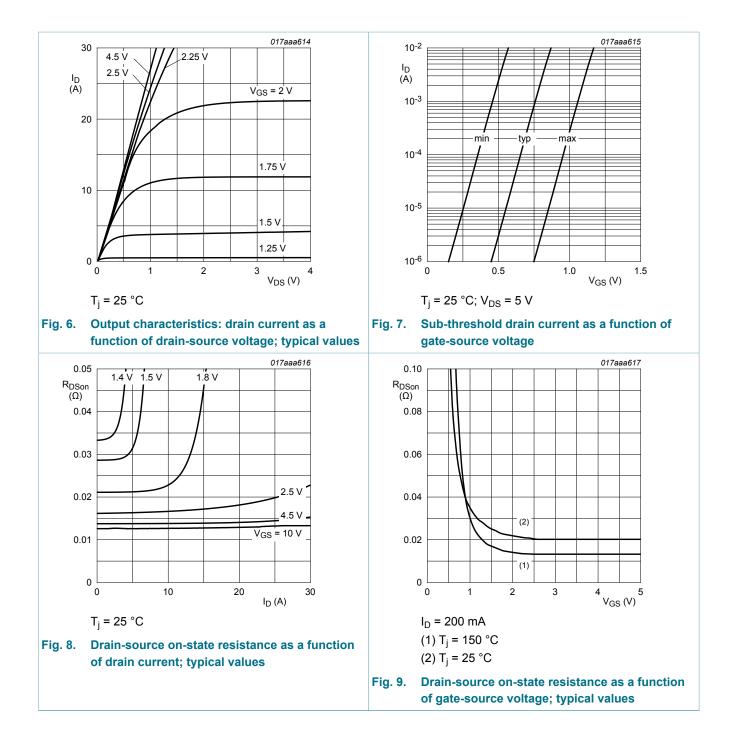
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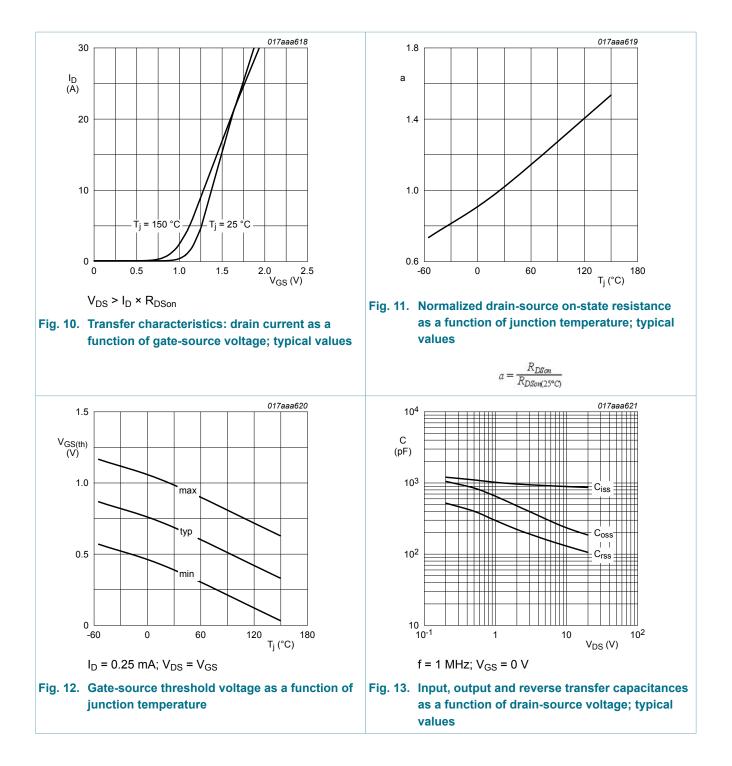
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 8 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
		$V_{GS}$ = -8 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = 4.5 V; I <sub>D</sub> = 7.9 A; T <sub>j</sub> = 25 °C	-	14	18	mΩ
	resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 7.9 A; T <sub>j</sub> = 150 °C	-	21	27	mΩ
		$V_{GS}$ = 2.5 V; I <sub>D</sub> = 3.5 A; T <sub>j</sub> = 25 °C	-	17	23	mΩ
		V <sub>GS</sub> = 1.8 V; I <sub>D</sub> = 3.5 A; T <sub>j</sub> = 25 °C	-	21	33	mΩ
9fs	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 7.9 A; T <sub>j</sub> = 25 °C	-	25	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	1.4	-	Ω
Dynamic cl	haracteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 10 V; I <sub>D</sub> = 6 A; V <sub>GS</sub> = 4.5 V; T <sub>j</sub> = 25 °C	-	8.8	13	nC
Q <sub>GS</sub>	gate-source charge		-	1	-	nC
Q <sub>GD</sub>	gate-drain charge		-	2.2	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS}$ = 10 V; f = 1 MHz; $V_{GS}$ = 0 V;	-	886	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	233	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	129	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 10 V; I <sub>D</sub> = 6 A; V <sub>GS</sub> = 4.5 V;	-	9	-	ns
t <sub>r</sub>	rise time	R <sub>G(ext)</sub> = 6 Ω; T <sub>j</sub> = 25 °C	-	20	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	26	-	ns
t <sub>f</sub>	fall time		-	26	-	ns
Source-dra	in diode	, , , , , , , , , , , , , , , , , , , ,	1			
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 1.8 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.6	1.2	V

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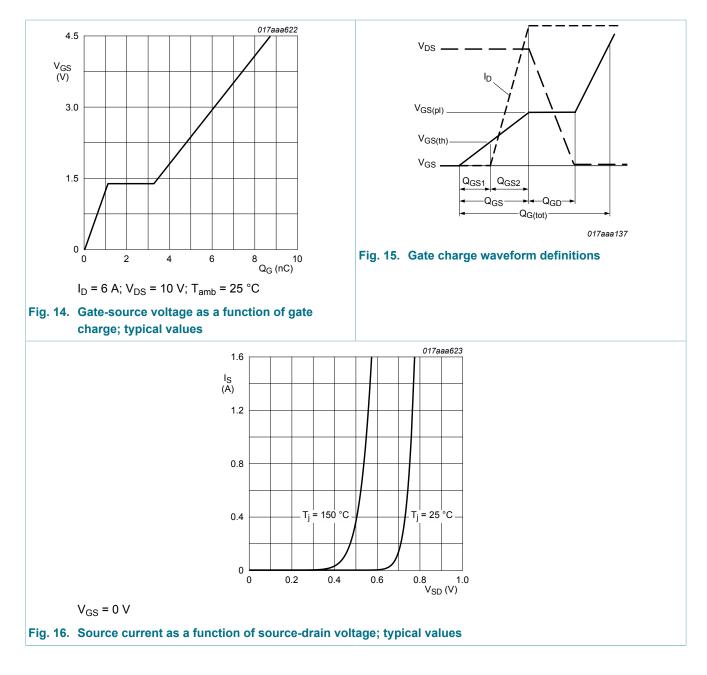


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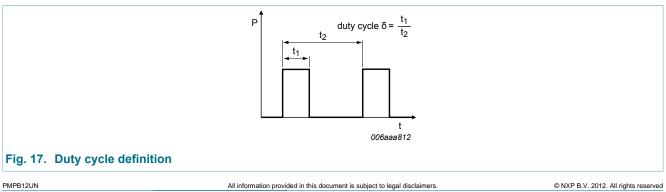


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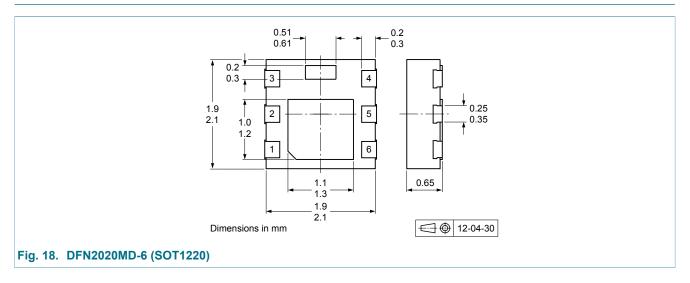


#### **Test information** 8.



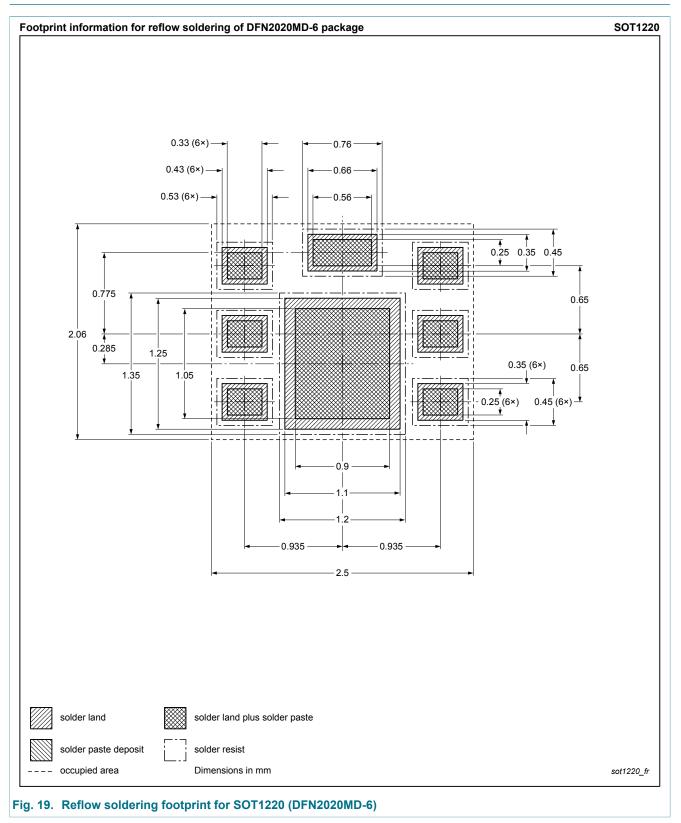
#### 20 V single N-channel Trench MOSFET

## 9. Package outline



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## **10. Soldering**



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## **11. Revision history**

Table 8.     Revision history								
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PMPB12UN v.1	20120706	Product data sheet	-	-				

#### 20 V single N-channel Trench MOSFET

#### 12. Legal information

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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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